

WHAT IS CLAIMED IS:

1. A thin film transistor including a plurality of component parts, comprising:  
a channel region;  
a gate electrode opposed to the channel region;  
a gate insulating film provided between the channel region and the gate electrode;  
a source-drain region connected to said channel region;  
a source-drain wiring layer electrically connected to said source-drain region;  
a gate wiring layer electrically connected to said gate electrode,  
an extension of the gate electrode extending outwardly above the channel region.
2. The thin film transistor according to claim 1, the extension extending from both ends of the gate electrode along a channel length direction.
3. The thin film transistor according to claim 1, the extension extending from at least one end of the gate electrode along a channel length direction.
4. The thin film transistor according to claim 3, the gate wiring layer being electrically connected to the extension of the at least one end of the gate electrode through a plurality of contact holes.
5. A CMOS inverter circuit comprising two of the thin film transistors according to claim 1, the thin film transistors having an inverse conductivity type from each other, adjacent source-drain regions of said thin film transistors being connected.
6. A display device comprising a driving circuit including a thin film transistor according to claim 1.
7. An electronic apparatus comprising a display device as defined in claim 6.